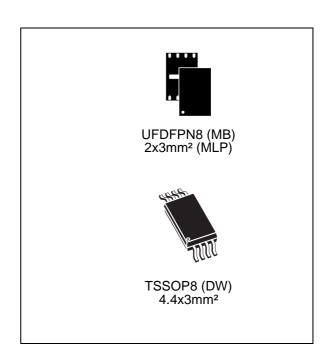


M34E02

2 Kbit Serial I²C Bus EEPROM with permanent and reversible, software Write protection

Feature summary

- Permanent and Reversible Software Data Protection for Lower 128 Bytes
- Two Wire I²C Serial Interface
- 400kHz Transfer Rate
- Very Low Voltage Operation:
 - 1.7 to 3.6V Single Supply Voltage
- Byte and Page Write (up to 16 Bytes)
- Self-Timed Write Cycle
- Noise filtering
 - Schmitt trigger on bus inputs
 - Noise filter on bus inputs
- Automatic Address Incrementing
- Enhanced ESD/Latch-Up Protection
- More than 1 Million Erase/Write Cycles
- More than 40 Years' Data Retention
- Packages
 - ECOPACK® (RoHS compliant)



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1 Summary description

The M34E02 is a 2 Kbit serial EEPROM memory able to lock permanently the data in its first half (from location 00h to 7Fh). This facility has been designed specifically for use in DRAM DIMMs (dual interline memory modules) with Serial Presence Detect. All the information concerning the DRAM module configuration (such as its access speed, its size, its organization) can be kept write protected in the first half of the memory.

The first half of the memory area can be write-protected using two different software write protection mechanisms. By sending the device a specific sequence, the first 128 bytes of the memory become write protected: permanently or resetable. In addition, the device allows the entire memory area to be write protected, using the $\overline{\text{WC}}$ input (for example by tieing this input to V_{CC}).

These I²C-compatible electrically erasable programmable memory (EEPROM) devices are organized as 256x8 bits.

I²C uses a two wire serial interface, comprising a bi-directional data line and a clock line. The device carries a built-in 4-bit Device Type Identifier code (1010) in accordance with the I²C bus definition to access the memory area and a second Device Type Identifier Code (0110) to define the protection. These codes are used together with the voltage level applied on the three chip enable inputs (E2, E1, E0).

The device behaves as a slave device in the I^2C protocol, with all memory operations synchronized by the serial clock. Read and Write operations are initiated by a START condition, generated by the bus master. The START condition is followed by a Device Select Code and $R\overline{W}$ bit (as described in *Table 2*), terminated by an acknowledge bit.

When writing data to the memory, the memory inserts an acknowledge bit during the 9th bit time, following the bus master's 8-bit transmission. When data is read by the bus master, the bus master acknowledges the receipt of the data byte in the same way. Data transfers are terminated by a STOP condition after an Ack for WRITE, and after a NoAck for READ.

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages.

ECOPACK® packages are Lead-free and RoHS compliant.

ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Figure 1. Logic diagram

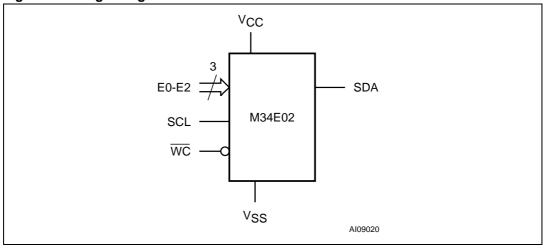
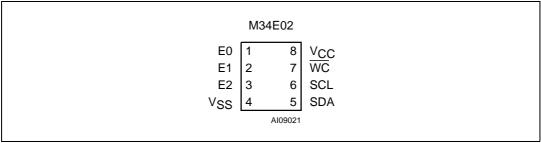


Figure 2. TSSOP and MLP connections (top view)



1. See the *Package mechanical* section for package dimensions, and how to identify pin-1.

Table 1. Signal names

<u> </u>	
E0, E1, E2	Chip Enable
SDA	Serial Data
SCL	Serial Clock
WC	Write Control
V _{CC}	Supply Voltage
V _{SS}	Ground

1.1 Internal device reset

In order to prevent inadvertent Write operations during Power-up, a Power On Reset (POR) circuit is included.

At Power-up (phase during which V_{CC} is lower than V_{CC} min but increases continuously), the device will not respond to any instruction until V_{CC} has reached the Power On Reset threshold voltage (this threshold is lower than the minimum V_{CC} operating voltage defined in the *DC and AC parameters* tables). Once V_{CC} has passed the POR threshold, the device is reset.

Prior to selecting the memory and issuing instructions, a valid and stable V_{CC} voltage must be applied. This voltage must remain stable and valid until the end of the transmission of the instruction and, for a Write instruction, until the completion of the internal write cycle (t_W) .

At Power-down (phase during which V_{CC} decreases continuously), as soon as V_{CC} drops from the normal operating voltage below the Power On Reset threshold voltage, the device stops responding to any instruction sent to it.

M34E02 Signal description

2 Signal description

2.1 Serial Clock (SCL)

This input signal is used to strobe all data in and out of the device. In applications where this signal is used by slave devices to synchronize the bus to a slower clock, the bus master must have an open drain output, and a pull-up resistor can be connected from Serial Clock (SCL) to V_{CC} . (*Figure 4* indicates how the value of the pull-up resistor can be calculated). In most applications, though, this method of synchronization is not employed, and so the pull-up resistor is not necessary, provided that the bus master has a push-pull (rather than open drain) output.

2.2 Serial Data (SDA)

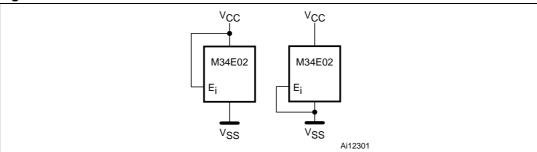
This bi-directional signal is used to transfer data in or out of the device. It is an open drain output that may be wire-OR'ed with other open drain or open collector signals on the bus. A pull up resistor must be connected from Serial Data (SDA) to V_{CC} . (*Figure 4* indicates how the value of the pull-up resistor can be calculated).

2.3 Chip Enable (E0, E1, E2)

These input signals are used to set the value that is to be looked for on the three least significant bits (b3, b2, b1) of the 7-bit Device Select Code. In the end application, E0, E1 and E2 must be directly (not through a pull-up or pull-down resistor) connected to V_{CC} or V_{SS} to establish the Device Select Code. When these inputs are not connected, an internal pull-down circuitry makes (E0,E1,E2) = (0,0,0).

The E0 input is used to detect the V_{HV} voltage, when decoding an SWP or CWP instruction.

Figure 3. Device Select Code



2.4 Write Control (WC)

This input signal is provided for protecting the contents of the whole memory from inadvertent write operations. Write Control (WC) is used to enable (when driven Low) or disable (when driven High) write instructions to the entire memory area or to the Protection Register.

When Write Control (\overline{WC}) is tied Low or left unconnected, the write protection of the first half of the memory is determined by the status of the Protection Register.

Signal description M34E02

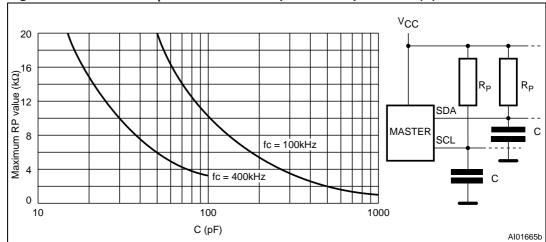
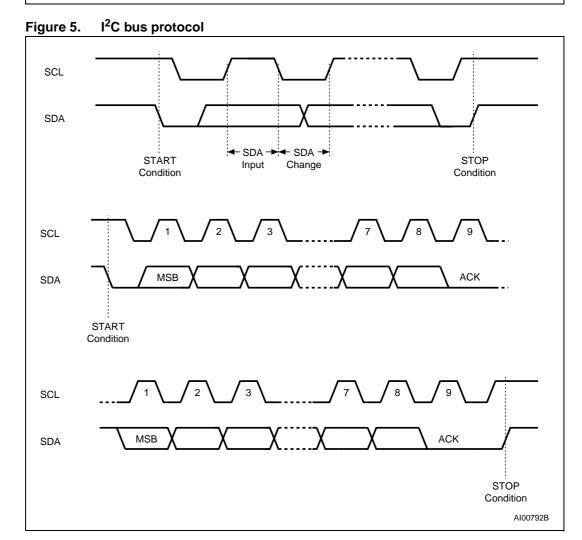


Figure 4. Maximum R_P value versus bus parasitic capacitance (C) for an I²C bus



M34E02 Signal description

Table 2. Device Select Code

		Chip Enable			Device Type Identifier			Chip Enable Bits			RW
	,	Signals	S	b7 ⁽¹⁾	b6	b5	b4	b3	b2	b1	b0
Memory Area Select Code (two arrays) ⁽²⁾	E2	E1	E0	1	0	1	0	E2	E1	E0	RW
Set Write Protection (SWP)	V _{SS}	V _{SS}	V _{HV}					0	0	1	0
Clear Write Protection (CWP)	V _{SS}	V _{CC}	V _{HV}					0	1	1	0
Permanently Set Write Protection (PSWP) ⁽²⁾	E2	E1	E0	0	1	1	0	E2	E1	E0	0
Read SWP	V _{SS}	V _{SS}	V_{HV}					0	0	1	1
Read CWP	V _{SS}	V _{CC}	V _{HV}					0	1	1	1
Read PSWP ⁽²⁾	E2	E1	E0					E2	E1	E0	1

^{1.} The most significant bit, b7, is sent first.

^{2.} E0, E1 and E2 are compared against the respective external pins on the memory device.

Device operation M34E02

3 Device operation

The device supports the I²C protocol. This is summarized in *Figure 5* Any device that sends data on to the bus is defined to be a transmitter, and any device that reads the data to be a receiver. The device that controls the data transfer is known as the bus master, and the other as the slave device. A data transfer can only be initiated by the bus master, which will also provide the serial clock for synchronization. The memory device is always a slave in all communication.

3.1 Start Condition

Start is identified by a falling edge of Serial Data (SDA) while Serial Clock (SCL) is stable in the High state. A Start condition must precede any data transfer command. The device continuously monitors (except during a Write cycle) Serial Data (SDA) and Serial Clock (SCL) for a Start condition, and will not respond unless one is given.

3.2 Stop Condition

Stop is identified by a rising edge of Serial Data (SDA) while Serial Clock (SCL) is stable and driven High. A Stop condition terminates communication between the device and the bus master. A Read command that is followed by NoAck can be followed by a Stop condition to force the device into the Standby mode. A Stop condition at the end of a Write command triggers the internal EEPROM Write cycle.

3.3 Acknowledge Bit (ACK)

The acknowledge bit is used to indicate a successful byte transfer. The bus transmitter, whether it be bus master or slave device, releases Serial Data (SDA) after sending eight bits of data. During the 9th clock pulse period, the receiver pulls Serial Data (SDA) Low to acknowledge the receipt of the eight data bits.

3.4 Data Input

During data input, the device samples Serial Data (SDA) on the rising edge of Serial Clock (SCL). For correct device operation, Serial Data (SDA) must be stable during the rising edge of Serial Clock (SCL), and the Serial Data (SDA) signal must change *only* when Serial Clock (SCL) is driven Low.

M34E02 Device operation

3.5 Memory addressing

To start communication between the bus master and the slave device, the bus master must initiate a Start condition. Following this, the bus master sends the Device Select Code, shown in *Table 2* (on Serial Data (SDA), most significant bit first).

The Device Select Code consists of a 4-bit Device Type Identifier, and a 3-bit Chip Enable "Address" (E2, E1, E0). To address the memory array, the 4-bit Device Type Identifier is 1010b; to access the write-protection settings, it is 0110b.

Up to eight memory devices can be connected on a single I^2C bus. Each one is given a unique 3-bit code on the Chip Enable (E0, E1, E2) inputs. When the Device Select Code is received, the device only responds if the Chip Enable Address is the same as the value on the Chip Enable (E0, E1, E2) inputs.

The 8^{th} bit is the Read/Write bit (RW). This bit is set to 1 for Read and 0 for Write operations.

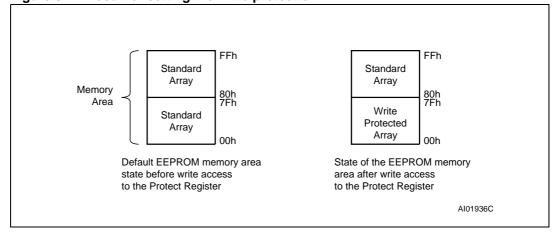
If a match occurs on the Device Select code, the corresponding device gives an acknowledgment on Serial Data (SDA) during the 9th bit time. If the device does not match the Device Select code, it deselects itself from the bus, and goes into Standby mode.

Table 3. Operating modes

Mode	R₩ bit	WC ⁽¹⁾	Bytes	Initial Sequence
Current Address Read	1	Х	1	START, Device Select, $R\overline{W} = 1$
Random Address Read	0	Х	1	START, Device Select, $R\overline{W} = 0$, Address
Random Address Read	1	Х	'	reSTART, Device Select, $R\overline{W} = 1$
Sequential Read	1	Х	≥ 1	Similar to Current or Random Address Read
Byte Write	0	V _{IL}	1	START, Device Select, $R\overline{W} = 0$
Page Write	0	V _{IL}	≤16	START, Device Select, $R\overline{W} = 0$

^{1.} $X = V_{IH}$ or V_{IL} .

Figure 6. Result of setting the write protection



Device operation M34E02

3.6 Setting the write-protection

The M34E02 has a hardware write-protection feature, using the Write Control (\overline{WC}) signal. This signal can be driven High or Low, and must be held constant for the whole instruction sequence. When Write Control (\overline{WC}) is held High, the whole memory array (addresses 00h to FFh) is write protected. When Write Control (\overline{WC}) is held Low, the write protection of the memory array is dependent on whether software write-protection has been set.

Software write-protection allows the bottom half of the memory area (addresses 00h to 7Fh) to be write protected irrespective of subsequent states of the Write Control (WC) signal.

Software write-protection is handled by three instructions:

- SWP: Set Write Protection
- CWP: Clear Write Protection
- PSWP: Permanently Set Write Protection

The level of write-protection (set or cleared) that has been defined using these instructions, remains defined even after a power cycle.

3.6.1 SWP and CWP

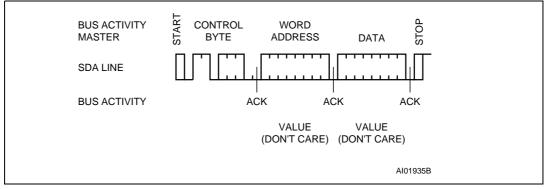
If the software write-protection has been set with the SWP instruction, it can be cleared again with a CWP instruction.

The two instructions (SWP and CWP) have the same format as a Byte Write instruction, but with a different Device Type Identifier (as shown in *Table 2*). Like the Byte Write instruction, it is followed by an address byte and a data byte, but in this case the contents are all "Don't Care" (*Figure 7*). Another difference is that the voltage, V_{HV}, must be applied on the E0 pin, and specific logical levels must be applied on the other two (E1 and E2, as shown in *Table 2*).

3.6.2 PSWP

If the software write-protection has been set with the PSWP instruction, the first 128 bytes of the memory are permanently write-protected. This write-protection cannot be cleared by any instruction, or by power-cycling the device, and regardless the state of Write Control (\overline{WC}) . Also, once the PSWP instruction has been successfully executed, the M34E02 no longer acknowledges any instruction (with a Device Type Identifier of 0110) to access the write-protection settings.

Figure 7. Setting the write protection ($\overline{WC} = 0$)



M34E02 Device operation

3.7 Write Operations

Following a Start condition the bus master sends a Device Select Code with the $R\overline{W}$ bit reset to 0. The device acknowledges this, as shown in *Figure 8*, and waits for an address byte. The device responds to the address byte with an acknowledge bit, and then waits for the data byte.

When the bus master generates a Stop condition immediately after the Ack bit (in the "10th bit" time slot), either at the end of a Byte Write or a Page Write, the internal memory Write cycle is triggered. A Stop condition at any other time slot does not trigger the internal Write cycle.

During the internal Write cycle, Serial Data (SDA) and Serial Clock (SCL) are ignored, and the device does not respond to any requests.

3.7.1 Byte Write

After the Device Select Code and the address byte, the bus master sends one data byte. If the addressed location is hardware write-protected, the device replies to the data byte with NoAck, and the location is not modified. If, instead, the addressed location is not Write-protected, the device replies with Ack. The bus master terminates the transfer by generating a Stop condition, as shown in *Figure 8*

3.7.2 Page Write

The Page Write mode allows up to 16 bytes to be written in a single Write cycle, provided that they are all located in the same page in the memory: that is, the most significant memory address bits are the same. If more bytes are sent than will fit up to the end of the page, a condition known as 'roll-over' occurs. This should be avoided, as data starts to become overwritten in an implementation dependent way.

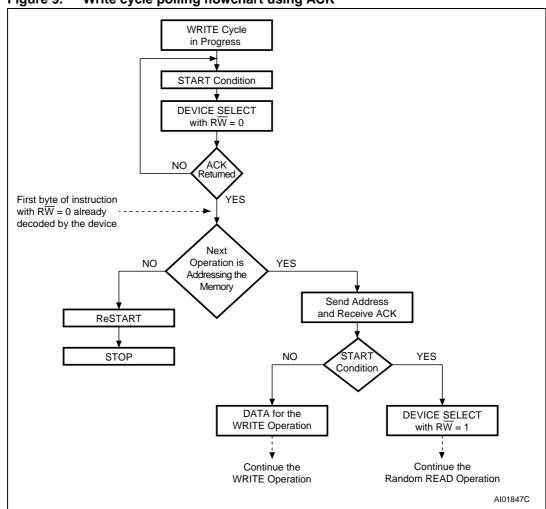
The bus master sends from 1 to 16 bytes of data, each of which is acknowledged by the device if Write Control (\overline{WC}) is Low. If the addressed location is hardware write-protected, the device replies to the data byte with NoAck, and the locations are not modified. After each byte is transferred, the internal byte address counter (the 4 least significant address bits only) is incremented. The transfer is terminated by the bus master generating a Stop condition.

Device operation M34E02

ACK ACK ACK BYTE ADDR DEV SEL DATA IN BYTE WRITE START STOP R/W ACK ACK **ACK** DEV SEL DATA IN 1 PAGE WRITE BYTE ADDR DATA IN 2 START R/W ACK ACK DATA IN N STOP AI01941

Figure 8. Write mode sequences in a non write-protected area

Figure 9. Write cycle polling flowchart using ACK



M34E02 Device operation

3.7.3 Minimizing system delays by polling on ACK

During the internal Write cycle, the device disconnects itself from the bus, and writes a copy of the data from its internal latches to the memory cells. The maximum Write time (t_w) is shown in *Table 12*, but the typical time is shorter. To make use of this, a polling sequence can be used by the bus master.

The sequence, as shown in Figure 9, is:

- Initial condition: a Write cycle is in progress.
- Step 1: the bus master issues a Start condition followed by a Device Select Code (the first byte of the new instruction).
- Step 2: if the device is busy with the internal Write cycle, no Ack will be returned and the bus master goes back to Step 1. If the device has terminated the internal Write cycle, it responds with an Ack, indicating that the device is ready to receive the second part of the instruction (the first byte of this instruction having been sent during Step 1).

Device operation M34E02

3.8 Read operations

Read operations are performed independently of whether hardware or software protection has been set.

The device has an internal address counter which is incremented each time a byte is read.

3.8.1 Random Address Read

A dummy Write is first performed to load the address into this address counter (as shown in *Figure 10*) but *without* sending a Stop condition. Then, the bus master sends another Start condition, and repeats the Device Select Code, with the $R\overline{W}$ bit set to 1. The device acknowledges this, and outputs the contents of the addressed byte. The bus master must *not* acknowledge the byte, and terminates the transfer with a Stop condition.

3.8.2 Current Address Read

For the Current Address Read operation, following a Start condition, the bus master only sends a Device Select Code with the RW bit set to 1. The device acknowledges this, and outputs the byte addressed by the internal address counter. The counter is then incremented. The bus master terminates the transfer with a Stop condition, as shown in *Figure 10*, *without* acknowledging the byte.

3.8.3 Sequential Read

This operation can be used after a Current Address Read or a Random Address Read. The bus master *does* acknowledge the data byte output, and sends additional clock pulses so that the device continues to output the next byte in sequence. To terminate the stream of bytes, the bus master must *not* acknowledge the last byte, and *must* generate a Stop condition, as shown in *Figure 10*.

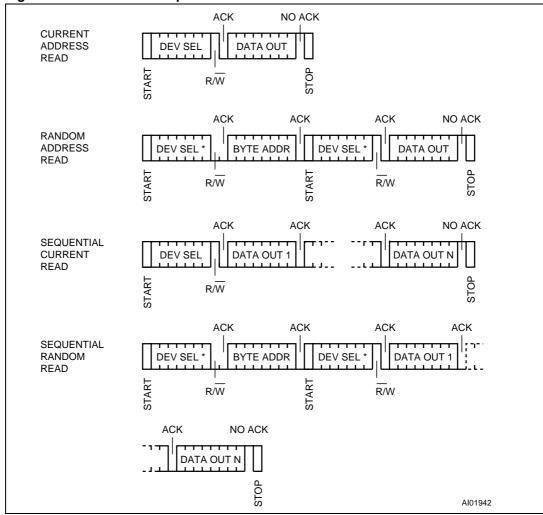
The output data comes from consecutive addresses, with the internal address counter automatically incremented after each byte output. After the last memory address, the address counter 'rolls-over', and the device continues to output data from memory address 00h.

3.8.4 Acknowledge in Read mode

For all Read commands, the device waits, after each byte read, for an acknowledgment during the 9th bit time. If the bus master does not drive Serial Data (SDA) Low during this time, the device terminates the data transfer and switches to its Standby mode.

M34E02 Device operation

Figure 10. Read mode sequences



The seven most significant bits of the Device Select Code of a Random Read (in the 1st and 3rd bytes) must be identical.

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Initial delivery state M34E02

4 Initial delivery state

The device is delivered with all bits in the memory array set to '1' (each Byte contains FFh).

5 Use within a DDR2 DIMM

In the application, the M34E02 is soldered directly in the printed circuit module. The three Chip Enable inputs (E0, E1, E2) must be connected to V_{SS} or V_{CC} directly (that is without using a pull-up or pull-down resistor) through the DIMM socket (see *Table 4*). The pull-up resistors needed for normal behavior of the I^2C bus are connected on the I^2C bus of the mother-board (as shown in *Figure 11*).

The Write Control (\overline{WC}) of the M34E02 can be left unconnected. However, connecting it to V_{SS} is recommended, to maintain full read and write access.

E2	E1	E0
V _{SS}	V _{SS}	V _{SS}
V _{SS}	V _{SS}	V _{CC}
V _{SS}	V _{CC}	V _{SS}
V _{SS}	V _{CC}	V _{CC}
V _{CC}	V _{SS}	V _{SS}
V _{CC}	V _{SS}	V _{CC}
V _{CC}	V _{CC}	V _{SS}
V _{CC}	V _{CC}	V _{CC}
	V _{SS} V _{SS} V _{SS} V _{SS} V _{CC} V _{CC} V _{CC}	Vss Vss Vss Vss Vss Vcc Vss Vcc Vcc Vss Vcc Vss Vcc Vss Vcc Vcc

Table 4. DRAM DIMM Connections

5.1 Programming the M34E02

The situations in which the M34E02 is programmed can be considered under two headings:

- when the DDR2 DIMM is isolated (not inserted on the PCB motherboard)
- when the DDR2 DIMM is inserted on the PCB motherboard

5.1.1 DDR2 DIMM isolated

With specific programming equipment, it is possible to define the M34E02 content, using Byte and Page Write instructions, and its write-protection using the SWP and CWP instructions. To issue the SWP and CWP instructions, the DDR2 DIMM must be inserted in the DDR2-specific slot where the E0 signal can be driven to V_{HV} during the whole instruction. This programming step is mainly intended for use by DDR2 DIMM makers, whose end application manufacturers will want to clear this write-protection with the CWP on their own specific programming equipment, to modify the lower 128 Bytes, and finally to set permanently the write-protection with the PSWP instruction.

5.1.2 DDR2 DIMM inserted in the application mother board

As the final application cannot drive the E0 pin to V_{HV} , the only possible action is to freeze the write-protection with the PSWP instruction.

Table 5 and *Table 6* show how the Ack bits can be used to identify the write-protection status.

Table 5. Acknowledge when writing data or defining the write-protection (instructions with R/W bit=0)

Status	WC Input Level	Instruction	Ack	Address	Ack	Data Byte	Ack	Write Cycle (t _W)
Permanently	Х	PSWP, SWP or CWP	NoAck	Not significant	NoAck	Not significant	NoAck	No
protected	^	Page or Byte Write in lower 128 Bytes	Ack	Address	Ack	Data	NoAck	No
		SWP	NoAck	Not significant	NoAck	Not significant	NoAck	No
		CWP	Ack	Not significant	Ack	Not significant	Ack	Yes
	0	PSWP	Ack	Not significant	Ack	Not significant	Ack	Yes
Protected with SWP		Page or Byte Write in lower 128 Bytes	Ack	Address	Ack	Data	NoAck	No
WILLI SVVP	1	SWP	NoAck	Not significant	NoAck	Not significant	NoAck	No
		CWP	Ack	Not significant	Ack	Not significant	NoAck	No
			PSWP	Ack	Not significant	Ack	Not significant	NoAck
		Page or Byte Write	Ack	Address	Ack	Data	NoAck	No
	0	PSWP, SWP or CWP	Ack	Not significant	Ack	Not significant	Ack	Yes
Not		Page or Byte Write	Ack	Address	Ack	Data	Ack	Yes
Protected	1	PSWP, SWP or CWP	Ack	Not significant	Ack	Not significant	NoAck	No
		Page or Byte Write	Ack	Address	Ack	Data	NoAck	No

Use within a DDR2 DIMM M34E02

Table 6. Acknowledge when reading the write protection (instructions with R/W bit=1)

Status	Instruction	Ack	Address	Ack	Data byte	Ack
Permanently protected	PSWP, SWP or CWP	NoAck	Not significant	NoAck	Not significant	NoAck
	SWP	NoAck	Not significant	NoAck	Not significant	NoAck
Protected with SWP	CWP	Ack	Not significant	NoAck	Not significant	NoAck
	PSWP	Ack	Not significant	NoAck	Not significant	NoAck
Not Protected	PSWP, SWP or CWP	Ack	Not significant	NoAck	Not significant	NoAck

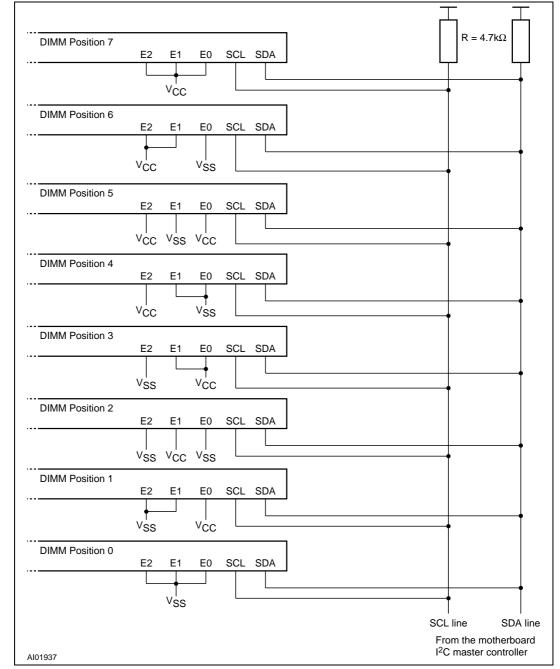


Figure 11. Serial presence detect block diagram

- 1. E0, E1 and E2 are wired at each DIMM socket in a binary sequence for a maximum of 8 devices.
- 2. Common clock and common data are shared across all the devices.
- 3. Pull-up resistors are required on all SDA and SCL bus lines (typically 4.7 $k\Omega$) because these lines are open drain when used as outputs.

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Maximum rating M34E02

6 Maximum rating

Stressing the device above the rating listed in the Absolute Maximum Ratings table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 7. Absolute maximum ratings

Symbol	Parameter		Min.	Max.	Unit
T _{STG}	Storage Temperature		-65	150	°C
V _{IO}	Input or Output range E0 Oth	iers	-0.50 -0.50	10.0 6.5	V
V _{CC}	Supply Voltage		-0.5	6.5	V
V _{ESD}	Electrostatic Discharge Voltage (Human Body mo	del) ⁽¹⁾	-4000	4000	V

^{1.} JEDEC Std JESD22-A114A (C1=100 pF, R1=1500 Ω , R2=500 Ω)

7 DC and AC parameters

This section summarizes the operating and measurement conditions, and the DC and AC characteristics of the device. The parameters in the DC and AC Characteristic tables that follow are derived from tests performed under the Measurement Conditions summarized in the relevant tables. Designers should check that the operating conditions in their circuit match the measurement conditions when relying on the quoted parameters.

Table 8. Operating conditions

Symbol	Parameter	Min.	Max.	Unit
V _{CC}	Supply Voltage	1.7	3.6	V
T _A	Ambient Operating Temperature	0	70	°C

Table 9. AC measurement conditions

Symbol	Parameter Min. Max.					
C _L	Load Capacitance 100					
	Input Rise and Fall Times 50					
	Input Levels	0.2V _{CC} to 0.8V _{CC} V				
	Input and Output Timing Reference Levels 0.3V _{CC} to 0.7V _{CC}					

Figure 12. AC measurement I/O waveform

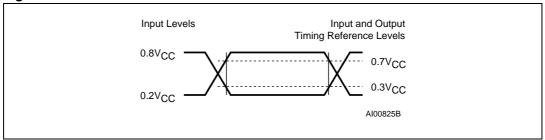


Table 10. Input parameters

Symbol	Parameter ⁽¹⁾⁽²⁾	Test Condition	Min.	Max.	Unit
C _{IN}	Input Capacitance (SDA)			8	pF
C _{IN}	Input Capacitance (other pins)			6	pF
Z _{EiL}	Ei (E0, E1, E2) Input Impedance	$V_{IN} < 0.3V_{CC}$	30		kΩ
Z _{EiH}	Ei (E0, E1, E2) Input Impedance	$V_{IN} > 0.7V_{CC}$	800		kΩ
Z _{WCL}	WC Input Impedance	V _{IN} < 0.3V _{CC}	5		kΩ
Z _{WCH}	WC Input Impedance	$V_{IN} > 0.7V_{CC}$	500		kΩ
t _{NS}	Pulse width ignored (Input Filter on SCL and SDA)			200	ns

^{1.} $T_A = 25 \, ^{\circ}\text{C}$, $f = 400 \, \text{kHz}$

Table 11. DC characteristics

Symbol	Parameter Test Condition (in addition to those in <i>Table 8</i>)		Min ⁽¹⁾	Max ⁽¹⁾	Unit
ILI	Input Leakage Current (SCL, SDA)	$V_{IN} = V_{SS}$ or V_{CC}		± 2	μΑ
I _{LO}	Output Leakage Current	$V_{OUT} = V_{SS}$ or V_{CC} , SDA in Hi-Z		± 2	μA
	Supply Current	V_{CC} =1.7V, f _c =100kHz (rise/fall time < 30ns)		1	mA
Icc	Supply Current	V_{CC} =3.6V, f _c =100kHz (rise/fall time < 30ns)		2	mA
1	Standby Supply Current	$V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 3.6V$		2	μA
I _{CC1}	Standby Supply Current	$V_{IN} = V_{SS}$ or V_{CC} , $V_{CC} = 1.7V$		1	μΑ
V _{IL}	Input Low Voltage (SCL, SDA, WC)		-0.45	0.3 V _{CC}	V
V _{IH}	Input High Voltage (SCL, SDA, WC)		0.7V _{CC}	V _{CC} +1	V
V _{HV}	E0 High Voltage	$V_{HV} - V_{CC} \ge 4.8V$	7	10	V
V	Output Low Voltage	$I_{OL} = 2.1 \text{mA}, 2.2 \text{V} \leq V_{CC} \leq 3.6 \text{V}$		0.4	V
V _{OL}	Output Low Voltage	$I_{OL} = 0.7 \text{mA}, V_{CC} = 1.7 \text{V}$		0.2	V

^{1.} Preliminary Data.

^{2.} Sampled only, not 100% tested.

Table 12. AC characteristics

Test conditions specified in Table 9 and Table 8						
Symbol	Alt.	Parameter	Min.	Max.	Unit	
f _C	f _{SCL}	Clock Frequency		400	kHz	
t _{CHCL}	t _{HIGH}	Clock Pulse Width High	600		ns	
t _{CLCH}	t _{LOW}	Clock Pulse Width Low	1300		ns	
t _{DL1DL2} ⁽¹⁾	t _F	SDA Fall Time	20	300	ns	
t _{DXCX}	t _{SU:DAT}	Data In Set Up Time	100		ns	
t _{CLDX}	t _{HD:DAT}	Data In Hold Time	0		ns	
t _{CLQX}	t _{DH}	Data Out Hold Time	200		ns	
t _{CLQV} ⁽²⁾	t _{AA}	Clock Low to Next Data Valid (Access Time)	200	900	ns	
t _{CHDX} (3)	t _{SU:STA}	Start Condition Set Up Time	600		ns	
t _{DLCL}	t _{HD:STA}	Start Condition Hold Time	600		ns	
t _{CHDH}	t _{SU:STO}	Stop Condition Set Up Time	600		ns	
t _{DHDL}	t _{BUF}	Time between Stop Condition and Next Start Condition	1300		ns	
t _W	t _{WR}	Write Time		10	ms	

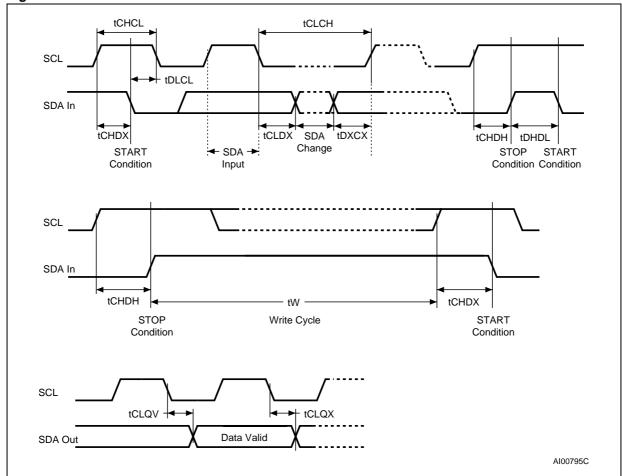
^{1.} Sampled only, not 100% tested.

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^{2.} To avoid spurious START and STOP conditions, a minimum delay is placed between SCL=1 and the falling or rising edge of SDA.

^{3.} For a reSTART condition, or following a Write cycle.

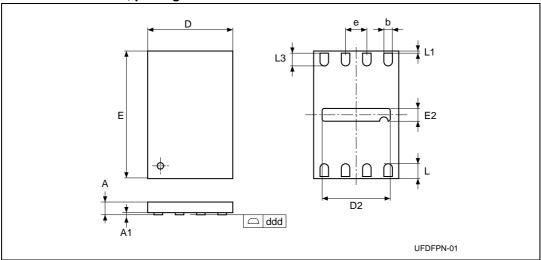
Figure 13. AC waveforms



M34E02 Package mechanical

8 Package mechanical

Figure 14. UFDFPN8 (MLP8) 8-lead Ultra thin Fine pitch Dual Flat Package No lead 2x3mm², package outline



- 1. Drawing is not to scale.
- The central pad (the area E2 by D2 in the above illustration) is pulled, internally, to V_{SS}. It must not be allowed to be connected to any other voltage or signal line on the PCB, for example during the soldering process.
- 3. The circle in the top view of the package indicates the position of pin 1.

Table 13. UFDFPN8 (MLP8) 8-lead Ultra thin Fine pitch Dual Flat Package No lead 2x3mm², package mechanical data

Symbol		millimeters		71			
Symbol	Тур.	Min.	Max.	Тур.	Min.	Max.	
А	0.55	0.50	0.60	0.022	0.020	0.024	
A1		0.00	0.05		0.000	0.002	
b	0.25	0.20	0.30	0.010	0.008	0.012	
D	2.00			0.079			
D2		1.55	1.65		0.061	0.065	
ddd			0.05			0.002	
Е	3.00			0.118			
E2		0.15	0.25		0.006	0.010	
е	0.50	_	-	0.020	-	_	
L	0.45	0.40	0.50	0.018	0.016	0.020	
L1			0.15			0.006	
L3		0.30			0.012		
N (number of pins)	umber of pins) 8 8						

Package mechanical M34E02

Figure 15. TSSOP8 – 8 lead Thin Shrink Small Outline, package outline

- 1. Drawing is not to scale.
- 2. The circle around the number 1 in the top view of the package indicates the position of pin 1. The numbers 4, 5 and 8 indicate the positions of pins 4, 5 and 8, respectively.

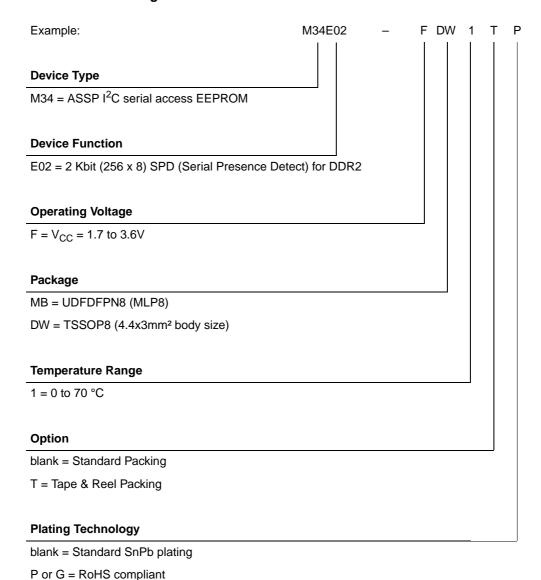
Table 14. TSSOP8 – 8 lead Thin Shrink Small Outline, Package Mechanical Data

Oh al		millimeters			inches	
Symbol	Тур.	Min.	Max.	Тур.	Min.	Max.
А			1.200			0.0472
A1		0.050	0.150		0.0020	0.0059
A2	1.000	0.800	1.050	0.0394	0.0315	0.0413
b		0.190	0.300		0.0075	0.0118
С		0.090	0.200		0.0035	0.0079
СР			0.100			0.0039
D	3.000	2.900	3.100	0.1181	0.1142	0.1220
е	0.650	_	-	0.0256	-	_
E	6.400	6.200	6.600	0.2520	0.2441	0.2598
E1	4.400	4.300	4.500	0.1732	0.1693	0.1772
L	0.600	0.450	0.750	0.0236	0.0177	0.0295
L1	1.000			0.0394		
α		0°	8°		0°	8°
N		8		8		

M34E02 Part numbering

9 Part numbering

Table 15. Ordering information scheme



For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST Sales Office.

The category of second-Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label.

Revision history M34E02

10 Revision history

Table 16. Document revision history

Date	Revision	Changes
13-Nov-2003	1.0	First release
01-Dec-2003	1.1	TSSOP8 4.4x3 package replaces TSSOP8 3x3 (MSOP8) package. Correction to sentence in "Setting the Write Protection". Correction to specification of t _{NS} values.
29-Mar-2004	1.2	Always NoACK after Address and Data bytes in <i>Table 6</i> . Improvement in V_{IO} and V_{CC} (min) in Absolute Maximum Ratings table. I_{OL} changed for test condition of V_{OL} . MLP package mechanical data respecified. Soldering temperature information clarified for RoHS compliant devices.
14-Apr-2004	2.0	First public release
24-Nov-2004	3.0	Direct connection of E0, E1, E2 to V _{SS} and V _{CC} (see <i>Chip Enable (E0, E1, E2)</i> and <i>Use within a DDR2 DIMM</i> paragraphs). Z _{EiL} and Z _{EiH} parameters added to <i>Table 10: Input parameters</i> . E0, E1, E2 removed from the Parameter descriptions of V _{IL} and V _{IH} in <i>Table 11: DC characteristics</i> . Document status promoted from Product Preview to full Datasheet.
11-Mar-2005	4.0	Datasheet title changed. Feature summary revised. Plating Technology options updated in Table 15: Ordering information scheme. Resistance and capacitance renamed in Figure 4: Maximum RP value versus bus parasitic capacitance (C) for an I2C bus.
28 -Apr-2005	5.0	Text in Power On Reset changed. Noise filter value in <i>Table 10: Input parameters</i> modified. I _{CC} value 2mA, when Vcc=3/6V, added to <i>Table 11: DC characteristics</i> .
10-Apr-2006	6	In <i>Table 12: AC characteristics</i> : Frequency f _C changed from 100kHz to 400kHz, related AC timings (t _{CHCL} , t _{CLCH} , t _{DXCX} , t _{CLQV} max, t _{CHDX} , t _{DLCL} , t _{CHDH} , t _{DHDL}) also modified. Power On Reset paragraph removed replaced by <i>Internal device reset</i> . <i>Figure 3: Device Select Code</i> inserted. I _{CC1} modified in <i>Table 11: DC characteristics</i> . Note 3 added to <i>Figure 14</i> and Note 2 added to <i>Figure 15</i> All packages are ECOPACK® (see text added under <i>Summary description</i> and <i>Part numbering</i> , T _{LEAD} removed from <i>Table 7: Absolute maximum ratings</i>).

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